

Amended Claims

1. (Amended) A method of forming an insulating material comprising:
providing a substrate within a reaction chamber at a temperature of from
about 400 degrees Celsius (°C) to about 700 °C;
providing reactants comprising silicon, fluorine and ozone within the reaction
chamber; and
depositing an insulating material, at a rate of from about 1000 angstroms per
minute (Å/min) to about 10000 Å/min, comprising fluorine, silicon and oxygen onto
the substrate from the reactants.

18. (Amended) A method of forming a silicon oxide having Si-F bonds,
comprising:
providing a substrate within a reaction chamber at a temperature of from
about 400 degrees Celsius (°C) to about 700 °C;
providing reactants comprising ozone and a precursor having Si-F bonds
within the reaction chamber; and
depositing a silicon oxide having Si-F bonds, at a rate of from about 1000
angstroms per minute (Å/min) to about 10000 Å/min, onto the substrate from the
reactants.

21. (Amended) A method of forming a boron-doped silicon oxide having
Si-F bonds, comprising:

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providing a substrate within a reaction chamber at a temperature of from
about 400 degrees Celsius (°C) to about 700 °C;

3 providing reactants comprising triethoxy fluorosilane, a boron-containing
4 precursor and ozone within the reaction chamber; and

5 depositing a boron-doped silicon oxide having Si-F bonds, at a rate of from
6 about 1000 angstroms per minute (Å/min) to about 10000 Å/min, onto the substrate
7 from the reactants.

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9 23. (Amended) A method of forming a phosphorus-doped silicon oxide
10 having Si-F bonds, comprising:

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11 providing a substrate within a reaction chamber at a temperature of from
12 about 400 degrees Celsius (°C) to about 700 °C;

13 providing reactants comprising triethoxy fluorosilane, a
14 phosphorus-containing precursor and ozone within the reaction chamber; and
15 depositing a phosphorus-doped silicon oxide having Si-F bonds, at a rate of
16 from about 1000 angstroms per minute (Å/min) to about 10000 Å/min, onto the
17 substrate from the reactants.

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19 25. (Amended) A method of forming a boron and phosphorus doped
20 silicon oxide having Si-F bonds, comprising:

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21 providing a substrate within a reaction chamber at a temperature of from
22 about 400 degrees Celsius (°C) to about 700 °C;
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3 providing reactants comprising triethoxy fluorosilane, a boron-containing
4 precursor, a phosphorus-containing precursor and ozone within the reaction
5 chamber; and
6 depositing a boron and phosphorus doped silicon oxide having Si-F bonds, at
7 a rate of from about 1000 angstroms per minute ($\text{\AA}/\text{min}$) to about 10000 $\text{\AA}/\text{min}$, onto
8 the substrate from the reactants, the depositing occurring without a plasma being
9 present in the reaction chamber.

10 New Claims

11 Add new claims 35-42 as follows:

12 --35. The method of claim 1 comprising maintaining a pressure within the
13 reaction chamber at about 600 Torr during the depositing.

14 36. The method of claim 1 comprising depositing the insulating material
15 at a rate of about 8000 $\text{\AA}/\text{min}$.

16 37. The method of claim 1 comprising providing a substrate within a
17 reaction chamber at a temperature of about 500 °C.

18 38. The method of claim 18 comprising maintaining a pressure within the
19 reaction chamber at from about 400 Torr to about 1 atmosphere during the
20 depositing.
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